Claims 1, 2 and 4-6 stand rejected under 35 U.S.C. § 102 and/or § 103 over Kang. This rejection is respectfully traversed.

The Examiner acknowledges in Section 7 of the Office Action that Kang does not disclose "an offset region formed on the whole lower region of the sidewall and substrate corresponding to the insulating film as a single region". Since claim 1 has been amended to recite this limitation, all claims should now be in condition for allowance.

For the foregoing reasons, reconsideration of the rejections of record is respectfully requested, and an early notice of allowance is earnestly solicited.

Conclusion

Attached hereto is a marked-up version of the changes made to the application by this Amendment.

Should there be any outstanding matters that need to be resolved in the present application, the Examiner is respectfully requested to contact Joseph A. Kolasch (Reg. No. 22,463) at the telephone number of the undersigned below, to conduct an interview in an effort to expedite prosecution in connection with the present application.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit

Account No. 02-2448 for any additional fees required under 37 C.F.R. §§ 1.16 or 1.17; particularly, extension of time fees.

Respectfully submitted,

BIRCH, STEWART, KOLASCH & BIRCH, LLP

By _____
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JAK/ALB:bb

Attachment: Version with Markings to Show Changes Made

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

The claims have been amended as follows:

1. (thrice amended) A thin film transistor, comprising:

a stepped substrate provided with a sidewall between upper and lower portions thereof;

an active layer formed on the stepped substrate;

a gate insulation film formed on a lower portion of the active layer and a sidewall of the active layer contiguous the lower portion of the active layer and sidewall of the stepped substrate, respectively;

an insulating film formed on a lower portion of the gate insulation film and a sidewall of the gate insulating film contiguous the lower portion of the gate insulating film and sidewall of the stepped substrate, respectively;

a gate electrode formed on the gate insulation film corresponding to the sidewalls of the substrate and the insulation film; ~~and~~

impurity regions in the active layer corresponding to the upper and lower portions of the substrate; and

an offset region formed on the whole lower region of the sidewall and substrate corresponding to the insulating film as a single region.

5. (amended) The thin film transistor of claim 1, wherein the insulation film is ~~an~~ ~~SOG (~~a spin-on-glass~~)~~ film.